



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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NPN HIGH POWER SILICON TRANSISTOR

Qualified per MIL-PRF-19500/488

Devices
2N5671
2N5672
Qualified Level

**JAN
JANTX
JANTXV**

MAXIMUM RATINGS

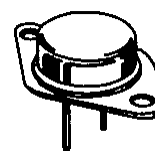
Ratings		Symbol	2N5671	2N5672	Unit
Collector-Emitter Voltage		V _{CEO}	90	120	Vdc
Collector-Base Voltage		V _{CBO}	120	150	Vdc
Emitter-Base Voltage		V _{EBO}	7.0		Vdc
Base Current		I _B	10		Adc
Collector Current		I _C	30		Adc
Total Power Dissipation	@ T _A = +25 ⁰ C ⁽¹⁾	P _T	6.0		W
	@ T _C = +25 ⁰ C ⁽²⁾		140		W
Operating & Storage Temperature Range		T _{op} , T _{stg}	-65 to +200		⁰ C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max.	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.25	$^{\circ}C/W$

1) Derate linearly 34.2 mW/ $^{\circ}C$ for $T_A > +25^{\circ}C$

2) Derate linearly 800 mW/ $^{\circ}C$ for $T_C > +25^{\circ}C$



TO-3*
(TO-204AA)

*See appendix A for package outline

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage $I_C = 200$ mAdc	2N5671 2N5672	$V_{(BR)CEO}$	90 120		Vdc
Collector-Emitter Breakdown Voltage $I_C = 200$ mAdc	2N5671 2N5672	$V_{(BR)CER}$	110 140		Vdc
Collector-Emitter Breakdown Voltage $I_C = 200$ mAdc	2N5671 2N5672	$V_{(BR)CEX}$	120 150		Vdc
Collector-Emitter Cutoff Current $V_{CE} = 80$ Vdc		I_{CEO}		10	mAdc
Collector-Emitter Cutoff Current $V_{CE} = 110$ Vdc, $V_{BE} = 1.5$ Vdc	2N5671	I_{CEX}		12	mAdc
$V_{CE} = 135$ Vdc, $V_{BE} = 1.5$ Vdc	2N5672			10	

ELECTRICAL CHARACTERISTICS (con't)

Characteristics	Symbol	Min.	Max.	Unit
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OFF CHARACTERISTICS (con't)

Collector-Base Cutoff Current V _{CB} = 120 Vdc V _{CB} = 150 Vdc	2N5671 2N5672	I _{CBO}	25 25	mAdc
Emitter-Base Cutoff Current V _{EB} = 7.0 Vdc		I _{EBO}	10	mAdc

ON CHARACTERISTICS ⁽³⁾

Forward-Current Transfer Ratio I _C = 15 Adc, V _{CE} = 2.0 Vdc I _C = 20 Adc, V _{CE} = 5.0 Vdc		h _{FE}	20 20	100	
Collector-Emitter Saturation Voltage I _C = 15 Adc, I _B = 1.2 Adc I _C = 30 Adc, I _B = 6.0 Adc		V _{CE(sat)}		0.75 5.0	Vdc
Base-Emitter Saturation Voltage I _C = 15 Adc, I _B = 1.2 Adc		V _{BE(sat)}		1.5	Vdc

DYNAMIC CHARACTERISTICS

Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio I _C = 2.0 Adc, V _{CE} = 10 Vdc, f = 5.0 MHz		h _{fe}	10	40	
Output Capacitance V _{CB} = 10 Vdc, I _E = 0, 100 kHz ≤ f ≤ 1.0 MHz		C _{obo}		900	pF

SWITCHING CHARACTERISTICS

Turn-On Time V _{CC} = 30 ± 2.0 Vdc; I _C = 15 Adc; I _{B1} = 1.2 Adc		t _{on}		0.5	μs
Turn-Off Time V _{CC} = 30 ± 2.0 Vdc; I _C = 15 Adc; I _{B1} = I _{B2} = 1.2 Adc		t _{off}		1.5	μs

SAFE OPERATING AREA

DC Tests T _C = +25°C, 1 Cycle, t = 1.0 s					
Test V _{CE} = 24 Vdc, I _C = 5.8 Adc					
Test 2 V _{CE} = 45 Vdc, I _C = 0.9 Adc					
Test 3 V _{CE} = 4.67 Vdc, I _C = 30 Adc					
Test 4 V _{CE} = 90 Vdc, I _C = 0.19 Adc					
2N5671					
Test 5 V _{CE} = 120 Vdc, I _C = 0.11 Adc					
2N5672					

(3) Pulse Test: Pulse Width = 300μs, Duty Cycle ≤ 2.0%.